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NTD4860N

MOSFET – Power, Single, N-Channel, DPAK/IPAK 25 V, 65 A

Features

- Trench Technology
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These are Pb-Free Devices

Applications

- VCore Applications
- DC-DC Converters
- High/Low Side Switching

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	25	V
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain Current R _{θJA} (Note 1)	Steady State	T _A = 25°C	I _D	13	A
		T _A = 85°C		10	
Power Dissipation R _{θJA} (Note 1)		T _A = 25°C	P _D	2.0	W
Continuous Drain Current R _{θJA} (Note 2)		T _A = 25°C	I _D	10.4	A
		T _A = 85°C		8.0	
Power Dissipation R _{θJA} (Note 2)		T _A = 25°C	P _D	1.28	W
Continuous Drain Current R _{θJC} (Note 1)		T _C = 25°C	I _D	65	A
		T _C = 85°C		50	
Power Dissipation R _{θJC} (Note 1)		T _C = 25°C	P _D	50	W
Pulsed Drain Current	t _p =10μs	T _A = 25°C	I _{DM}	130	A
Current Limited by Package		T _A = 25°C	I _{DmaxPkg}	45	A
Operating Junction and Storage Temperature			T _J , T _{STG}	-55 to +175	°C
Source Current (Body Diode)			I _S	42	A
Drain to Source dV/dt			dV/dt	6	V/ns
Single Pulse Drain-to-Source Avalanche Energy (T _J = 25°C, V _{DD} = 50 V, V _{GS} = 10 V, I _L = 13 A _{pk} , L = 1.0 mH, R _G = 25 Ω)			EAS	84.5	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

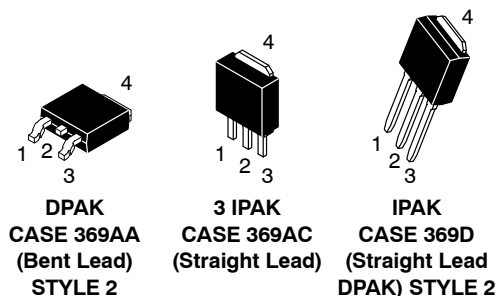
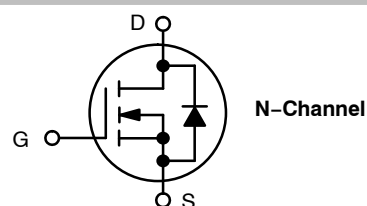
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



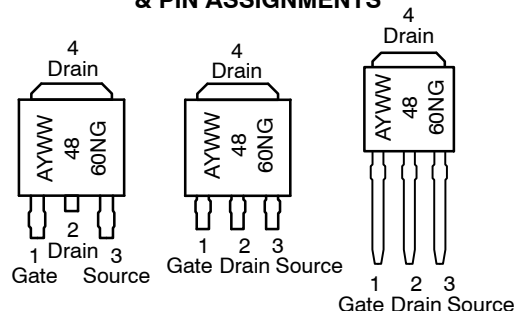
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$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
25 V	7.5 m Ω @ 10 V	65 A
	11.1 m Ω @ 4.5 V	



MARKING DIAGRAMS & PIN ASSIGNMENTS



A = Assembly Location*
Y = Year
WW = Work Week
4860N = Device Code
G = Pb-Free Package

* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	3	°C/W
Junction-to-TAB (Drain)	$R_{\theta JC-TAB}$	3.5	
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	75	
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	117	

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	25			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			21		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 20\text{ V}$			1.0	μA
		$T_J = 125^\circ\text{C}$			10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.45		2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			5.2		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		6.1	7.5	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 30\text{ A}$		8.9	11.1	
Forward Transconductance	g_{FS}	$V_{DS} = 1.5\text{ V}, I_D = 15\text{ A}$		48		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 12\text{ V}$		1308		pF
Output Capacitance	C_{OSS}			342		
Reverse Transfer Capacitance	C_{RSS}			169		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		11	16.5	nC
Threshold Gate Charge	$Q_{G(TH)}$			1.2		
Gate-to-Source Charge	Q_{GS}			3.9		
Gate-to-Drain Charge	Q_{GD}			4.7		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		21.8		nC

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\text{ }\Omega$		12.2		ns
Rise Time	t_r			20.1		
Turn-Off Delay Time	$t_{d(OFF)}$			15.2		
Fall Time	t_f			4.3		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
4. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 15\text{ A}, R_G = 3.0\ \Omega$		7.1		ns
Rise Time	t_r			17		
Turn-Off Delay Time	$t_{d(OFF)}$			22		
Fall Time	t_f			2.3		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 30\text{ A}$	$T_J = 25^{\circ}\text{C}$		0.9	1.2	V
			$T_J = 125^{\circ}\text{C}$		0.76		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 30\text{ A}$			12.7		ns
Charge Time	t_a				7.0		
Discharge Time	t_b				5.7		
Reverse Recovery Charge	Q_{RR}				3.5		nC

PACKAGE PARASITIC VALUES

Source Inductance	L_S	$T_A = 25^\circ\text{C}$		2.49		nH
Drain Inductance, DPAK	L_D			0.0164		
Drain Inductance, IPAK	L_D			1.88		
Gate Inductance	L_G			3.46		
Gate Resistance	R_G			0.75		Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

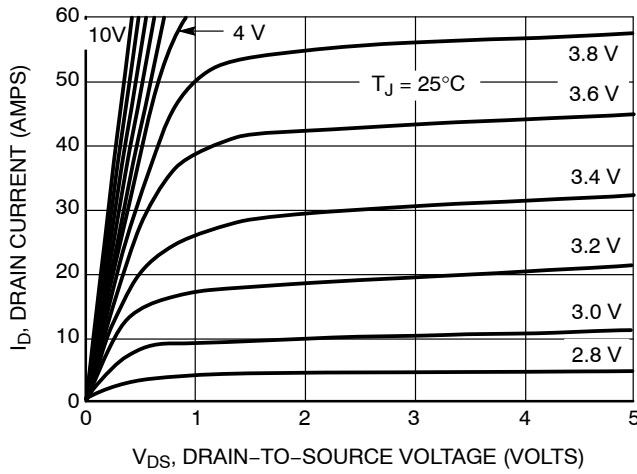


Figure 1. On-Region Characteristics

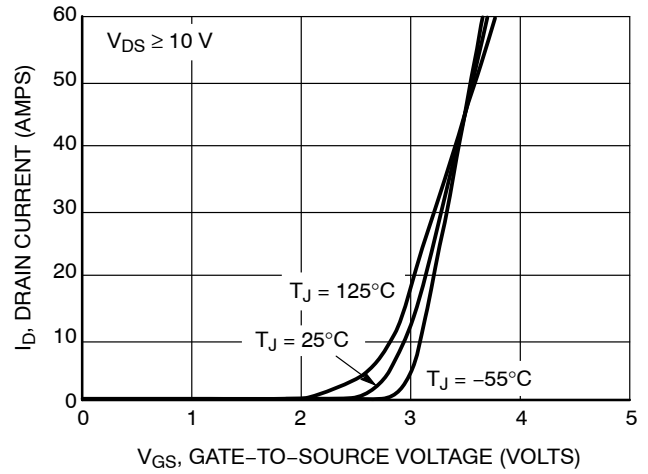


Figure 2. Transfer Characteristics

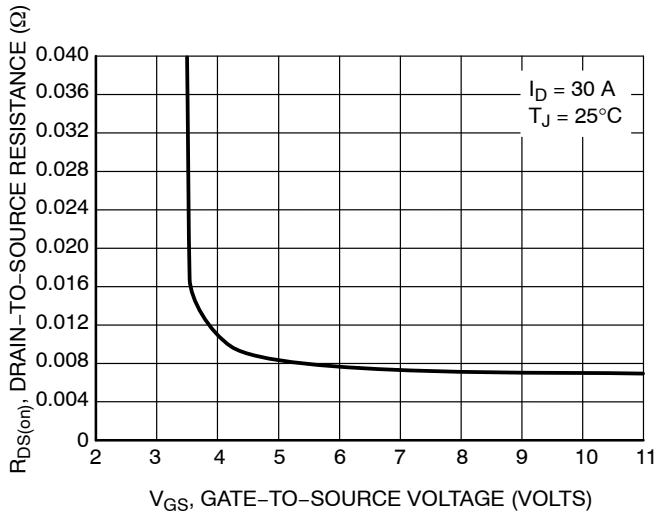


Figure 3. On-Resistance vs. Gate-to-Source Voltage

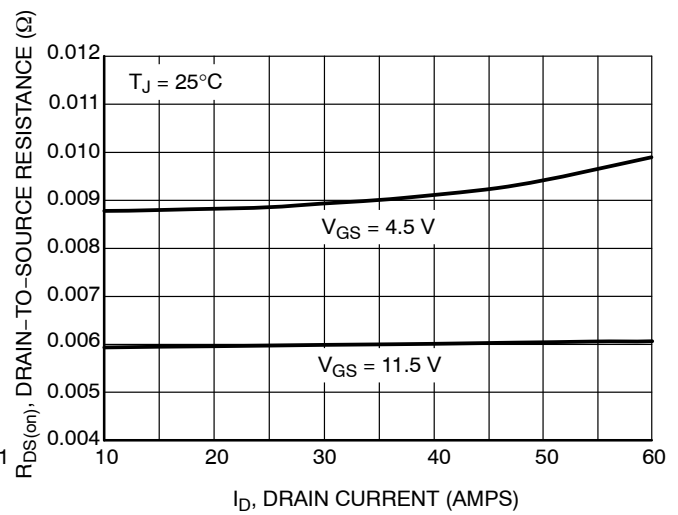


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

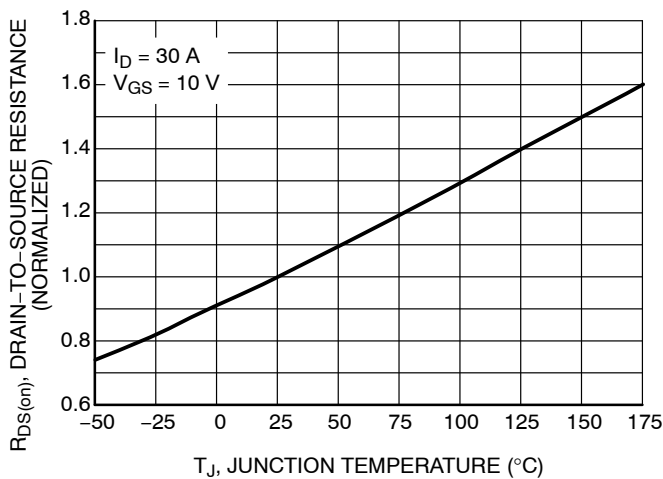


Figure 5. On-Resistance Variation with Temperature

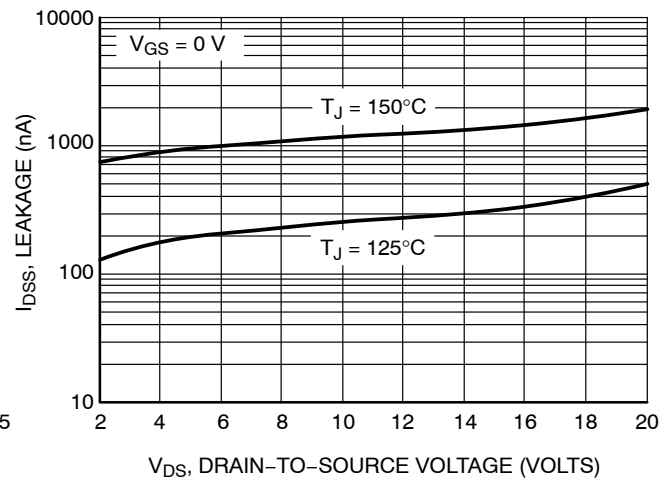


Figure 6. Drain-to-Source Leakage Current vs. Drain Voltage

TYPICAL PERFORMANCE CURVES

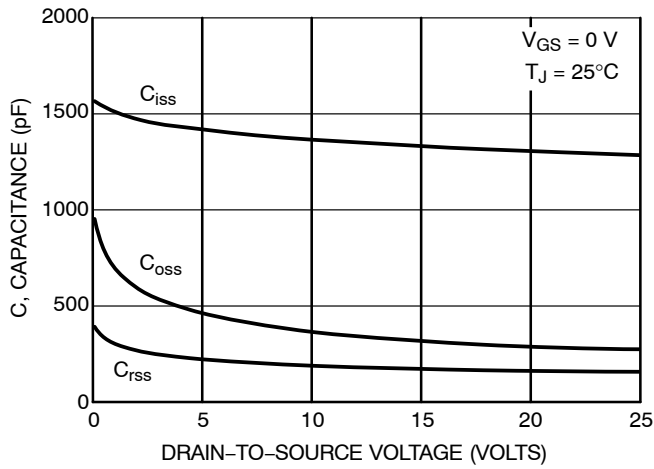


Figure 7. Capacitance Variation

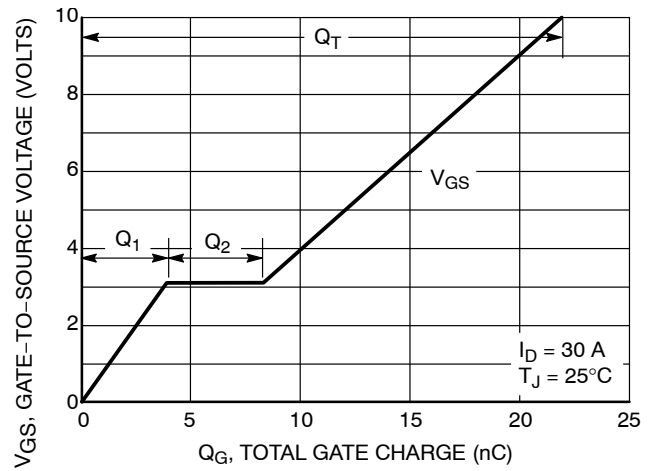


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

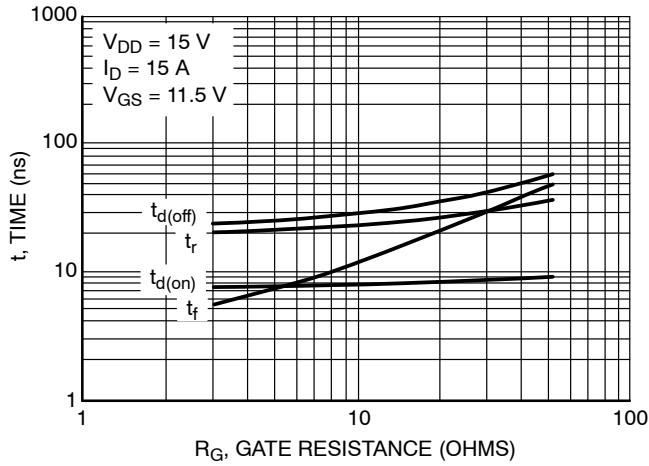


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

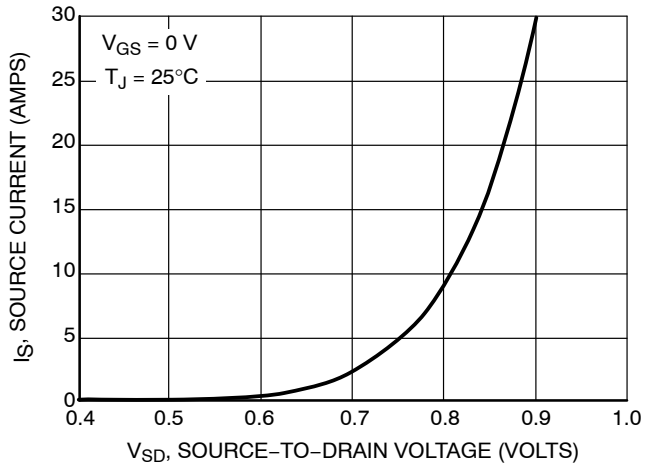


Figure 10. Diode Forward Voltage vs. Current

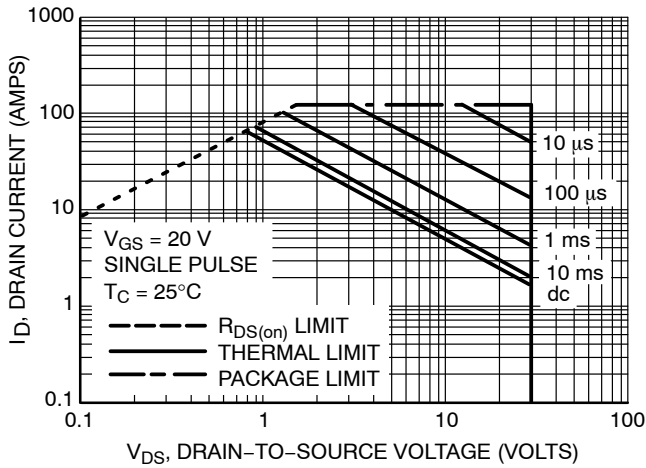


Figure 11. Maximum Rated Forward Biased Safe Operating Area

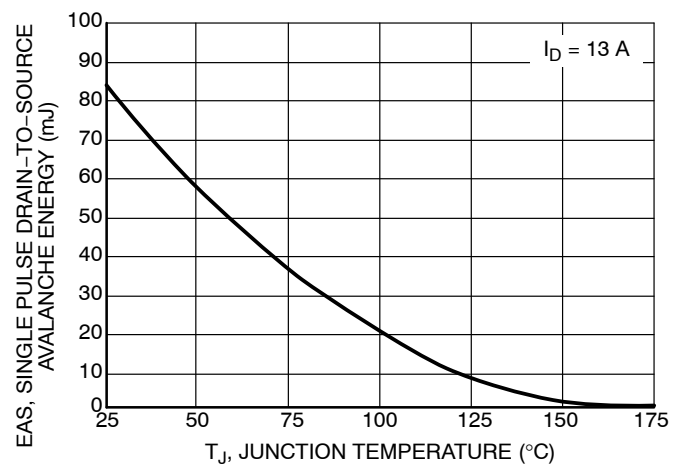


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

NTD4860N

TYPICAL PERFORMANCE CURVES

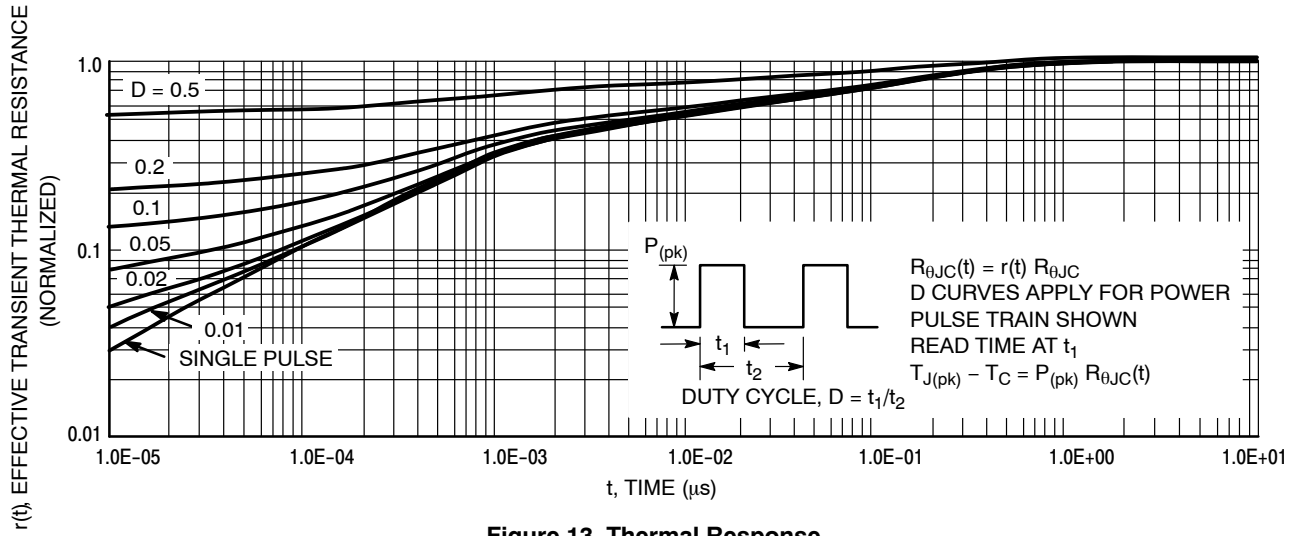


Figure 13. Thermal Response

ORDERING INFORMATION

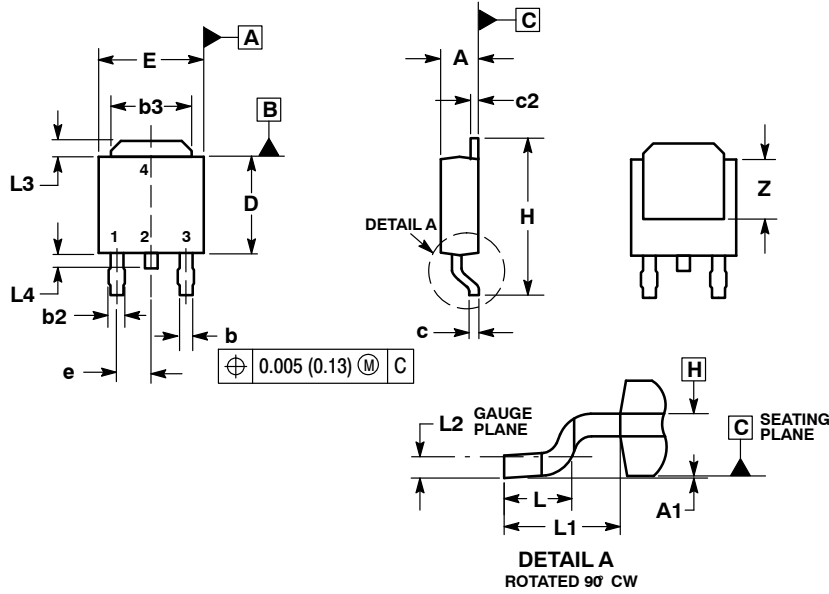
Device	Package	Shipping [†]
NTD4860NT4G	DPAK (Pb-Free)	2500 / Tape & Reel
NTD4860N-1G	IPAK (Pb-Free)	75 Units / Rail
NTD4860N-35G	IPAK Trimmed Lead (3.5 ± 0.15 mm) (Pb-Free)	75 Units / Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTD4860N

PACKAGE DIMENSIONS

DPAK (SINGLE GUAGE) CASE 369AA ISSUE B

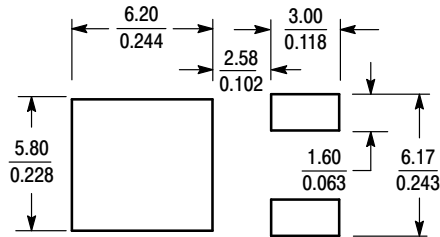


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT*



SCALE 3:1 ($\frac{\text{mm}}{\text{inches}}$)

STYLE 2:

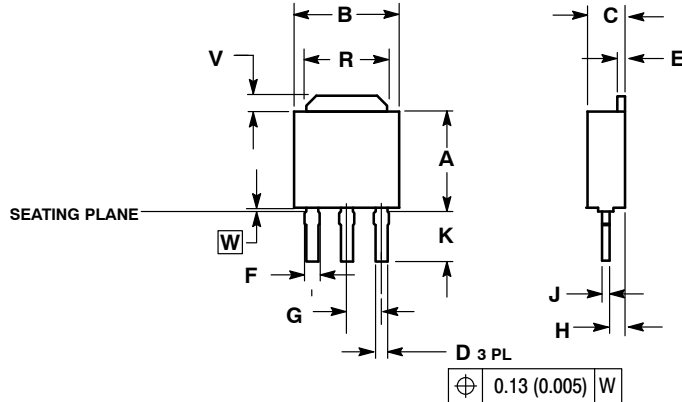
- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PACKAGE DIMENSIONS

3 IPAK, STRAIGHT LEAD CASE 369AC ISSUE O

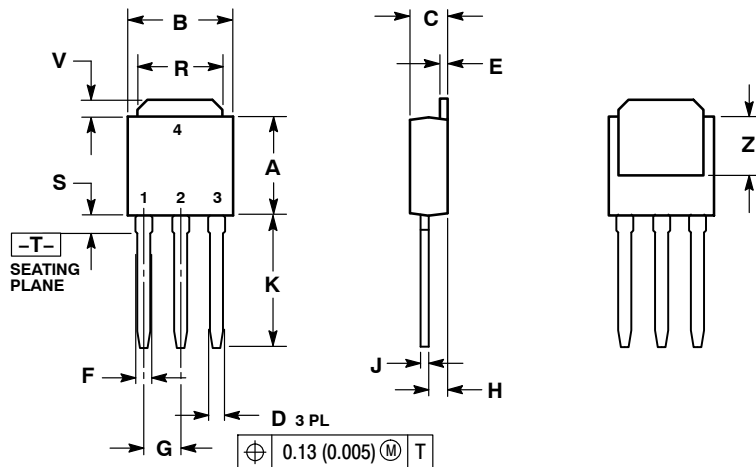


NOTES:

- 1.. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2.. CONTROLLING DIMENSION: INCH.
3. SEATING PLANE IS ON TOP OF DAMBAR POSITION.
4. DIMENSION A DOES NOT INCLUDE DAMBAR POSITION OR MOLD GATE.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.043	0.94	1.09
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.134	0.142	3.40	3.60
R	0.180	0.215	4.57	5.46
V	0.035	0.050	0.89	1.27
W	0.000	0.010	0.000	0.25

IPAK CASE 369D ISSUE C



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155		3.93	

STYLE 2:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

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